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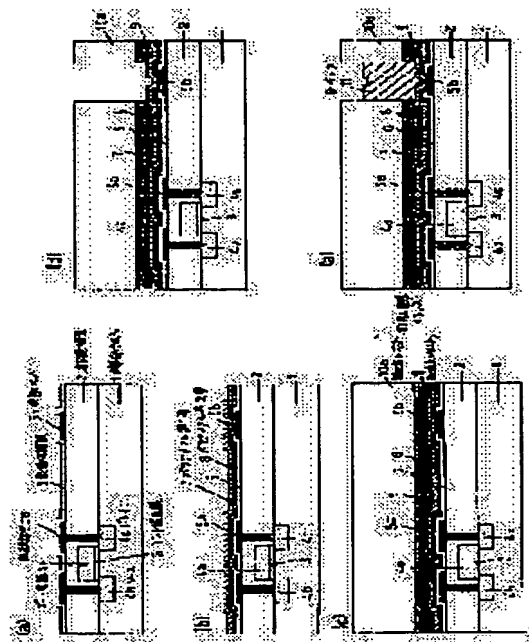
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(54) PRODUCTION OF SEMICONDUCTOR DEVICE

(57)Abstract:

PROBLEM TO BE SOLVED: To prevent the generation of cavities in dents and the resultant formation of resist holes when resists of large film thicknesses are formed in the level difference portions of the dents, etc., on a semiconductor integrated circuit device.

SOLUTION: The narrow dents are formed on the surface of a barrier metal second layer 8 for forming gold bumps 11 between wiring parts 5a of MOS transistors in this process for production. While a wafer 1 is heated, the low-temperature resist 9 is first applied thereon and thereafter, the high-viscosity resist 10a is applied thereon, by which the resist materials are packed into the dents as well. Coverage is thus improved and the generation of the cavities and the resist holes after baking are eliminated. The resist 10 of the large film thickness for forming the selective plating of the gold bumps may be assured by the high-viscosity resist 10a.



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